

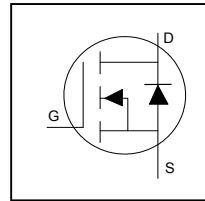
Features

- Advanced Process Technology
- Ultra Low On-Resistance
- Enhanced dV/dT and dI/dT capability
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *

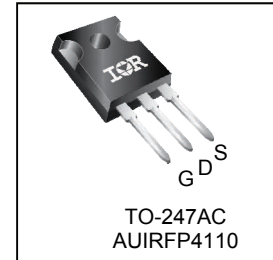
Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

HEXFET® Power MOSFET



V_{DSS}	100V
R_{DS(on)} typ.	3.7mΩ
	max
I_D (Silicon Limited)	180A①
I_D (Package Limited)	120A



G	D	S
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRFP4110	TO-247AC	Tube	25	AUIRFP4110

Absolute Maximum Ratings

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V (Silicon Limited)	180①	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V (Silicon Limited)	130①	
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V (Package Limited)	120	
I _{DM}	Pulsed Drain Current ②	670	
P _D @ T _C = 25°C	Maximum Power Dissipation	370	W
	Linear Derating Factor	2.5	W/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
E _{AS} (Thermally limited)	Single Pulse Avalanche Energy ③	190	mJ
I _{AR}	Avalanche Current ②	108	A
E _{AR}	Repetitive Avalanche Energy ⑤	37	mJ
dv/dt	Peak Diode Recovery ④	5.3	V/ns
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting Torque, 6-32 or M3 Screw	10 lbf·in (1.1 N·m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case ⑧	—	0.402	°C/W
R _{θCS}	Case-to-Sink, Flat Greased Surface	0.24	—	
R _{θJA}	Junction-to-Ambient	—	40	

HEXFET® is a registered trademark of Infineon.

*Qualification standards can be found at www.infineon.com


Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	100	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.108	—	V/°C	Reference to 25°C, I _D = 5mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	3.7	4.5	mΩ	V _{GS} = 10V, I _D = 75A ⑤
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Trans conductance	160	—	—	S	V _{DS} = 50V, I _D = 75A
I _{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	V _{DS} = 100V, V _{GS} = 0V
		—	—	250		V _{DS} = 100V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
R _G	Gate Resistance	—	1.3	—	Ω	

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

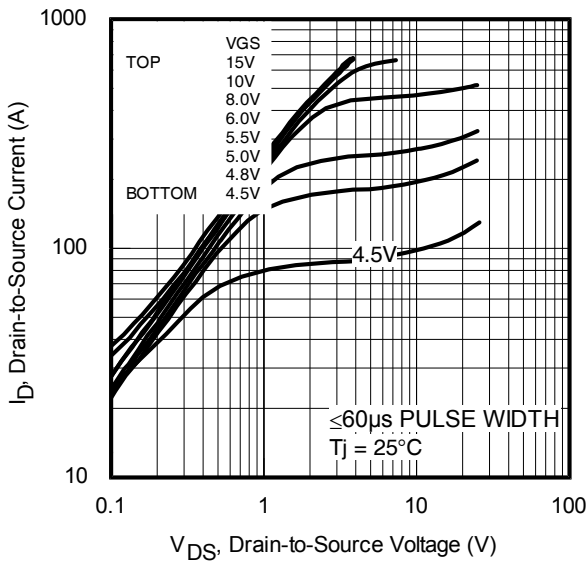
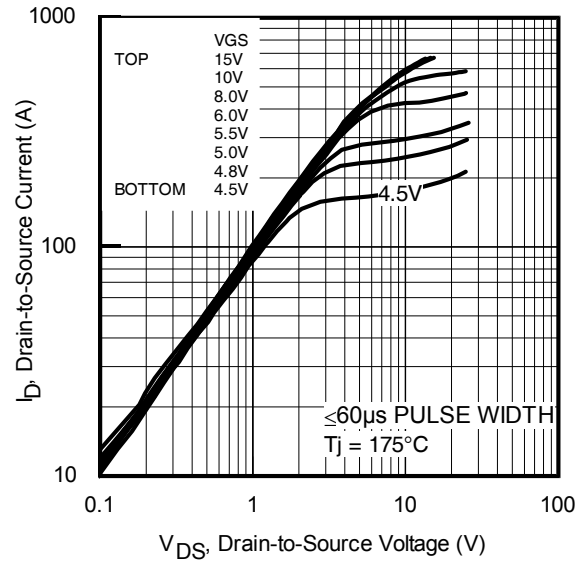
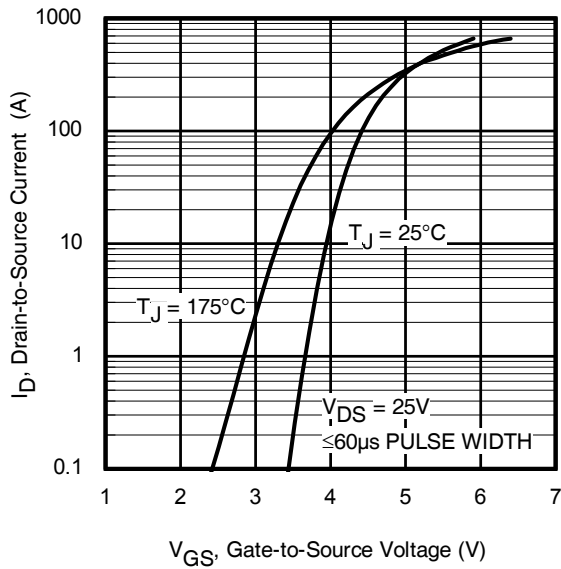
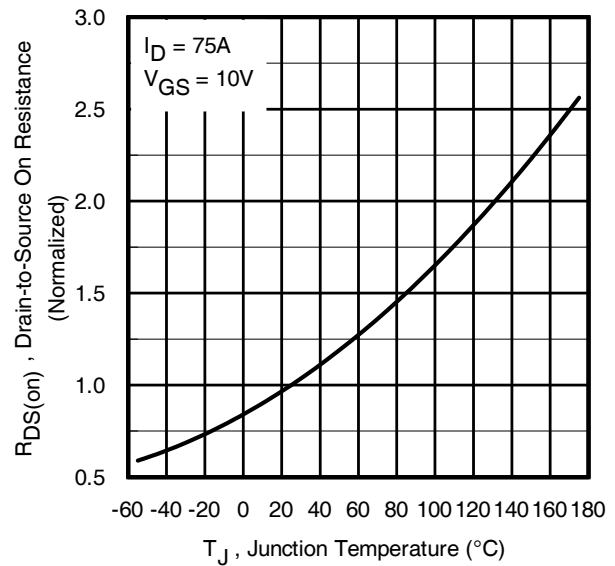
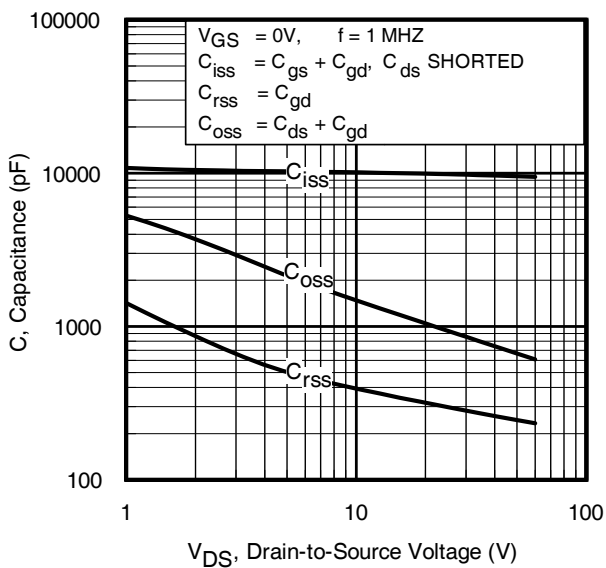
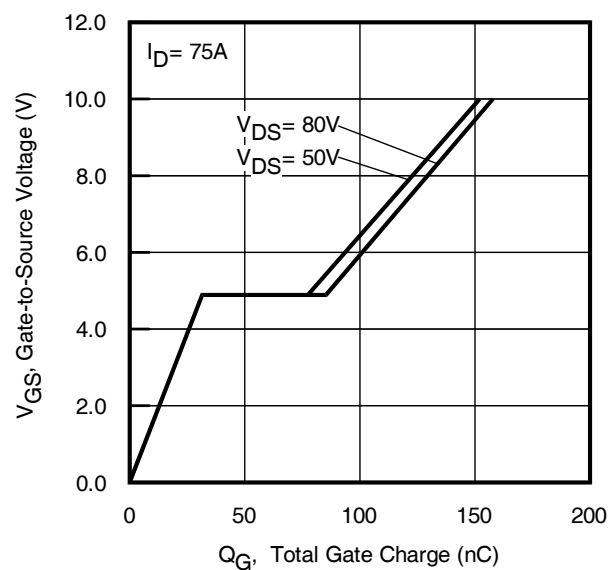
Q _g	Total Gate Charge	—	150	210	nC	I _D = 75A
Q _{gs}	Gate-to-Source Charge	—	35	—		V _{DS} = 50V
Q _{gd}	Gate-to-Drain Charge	—	43	—		V _{GS} = 10V ⑤
t _{d(on)}	Turn-On Delay Time	—	25	—	ns	V _{DD} = 65V
t _r	Rise Time	—	67	—		I _D = 75A
t _{d(off)}	Turn-Off Delay Time	—	78	—		R _G = 2.6Ω
t _f	Fall Time	—	88	—		V _{GS} = 10V ⑤
C _{iss}	Input Capacitance	—	9620	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	670	—		V _{DS} = 50V
C _{rss}	Reverse Transfer Capacitance	—	250	—		f = 1.0MHz
C _{oss eff.(ER)}	Effective Output Capacitance (Energy Related)	—	820	—		V _{GS} = 0V, V _{DS} = 0V to 80V ⑦
C _{oss eff.(TR)}	Output Capacitance (Time Related)	—	950	—		V _{GS} = 0V, V _{DS} = 0V to 80V ⑧

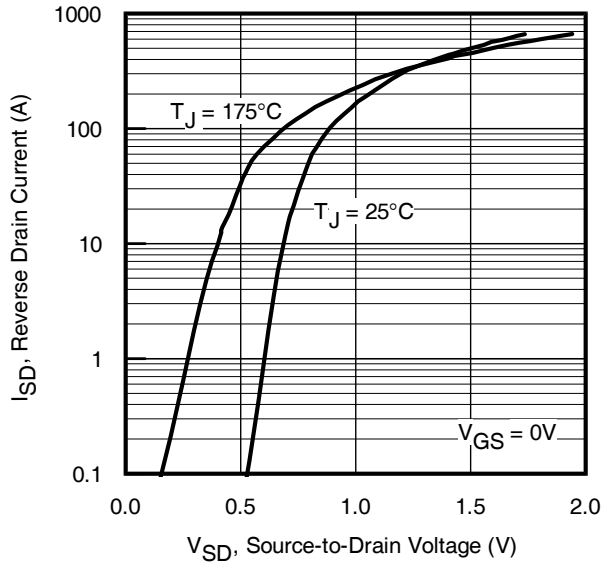
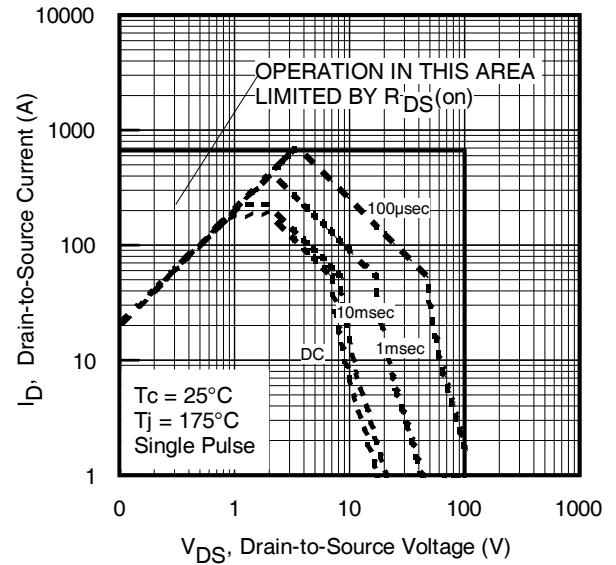
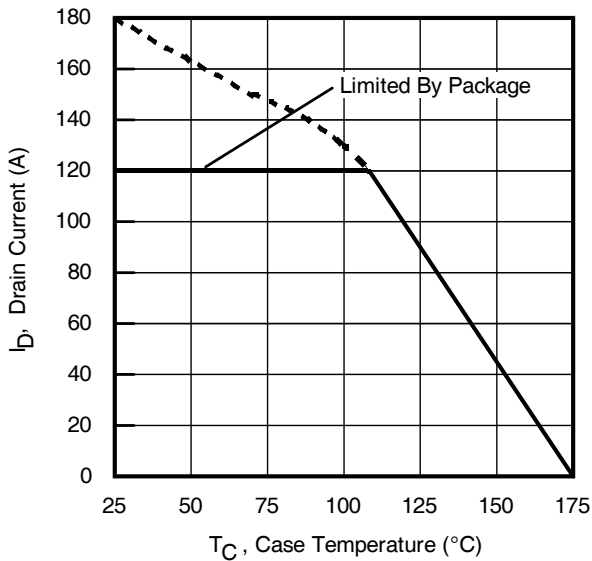
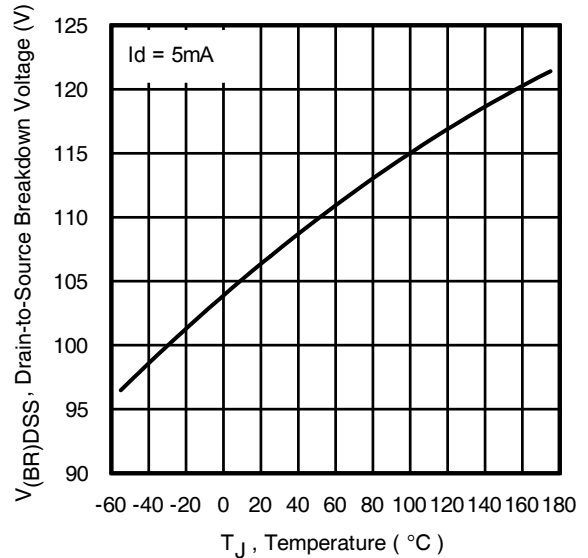
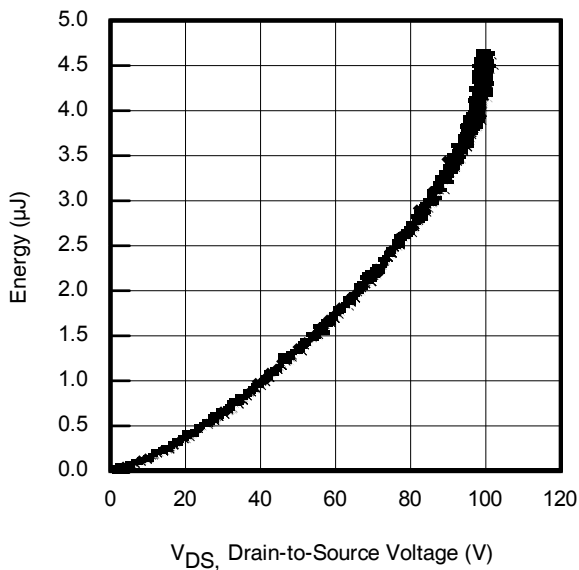
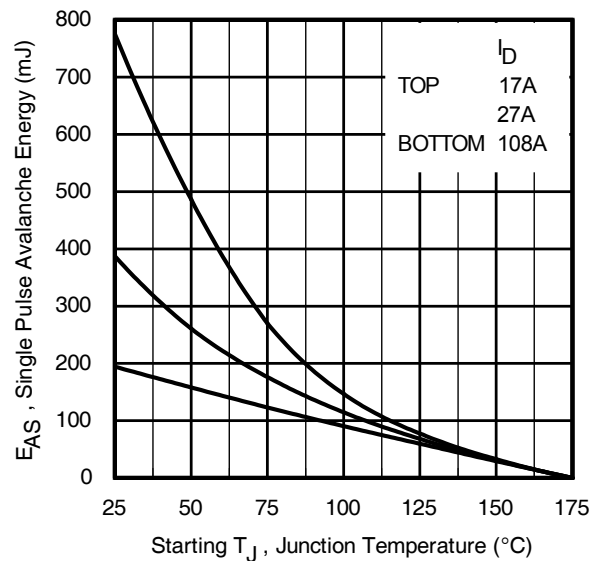
Diode Characteristics

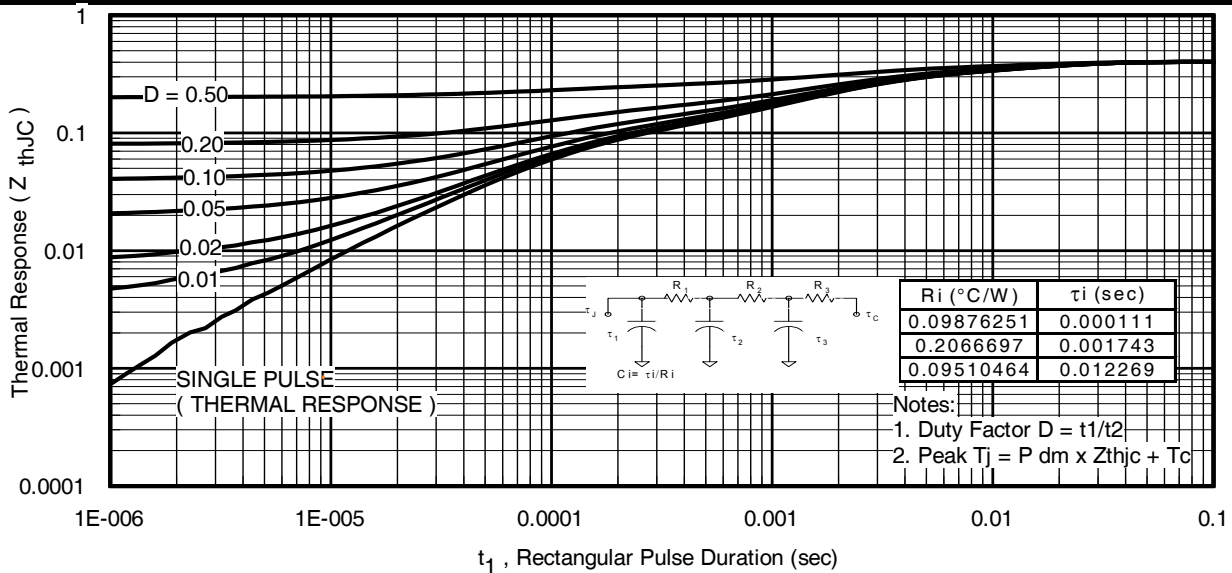
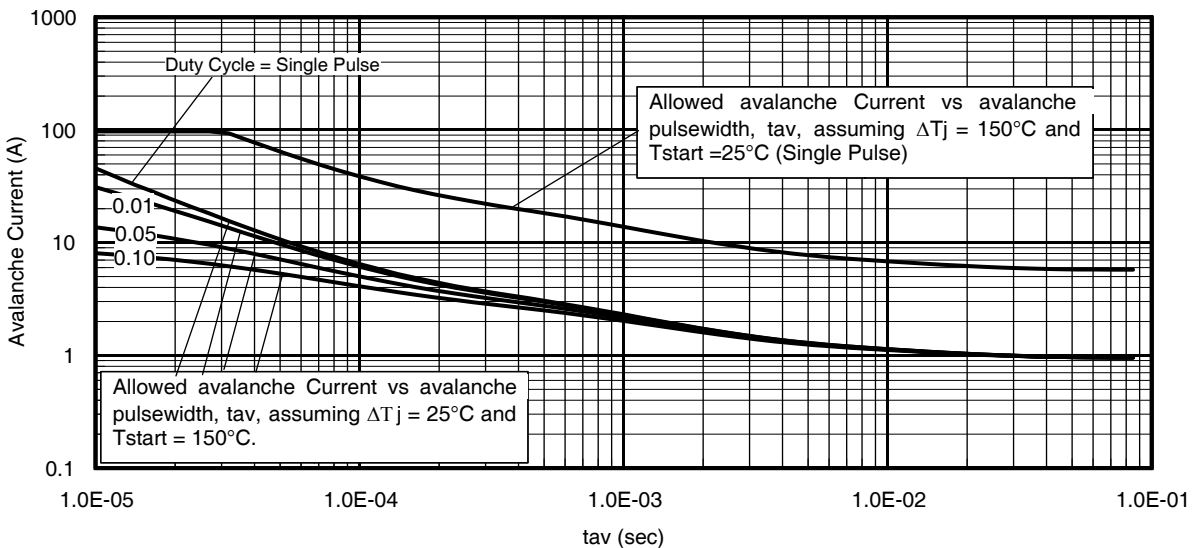
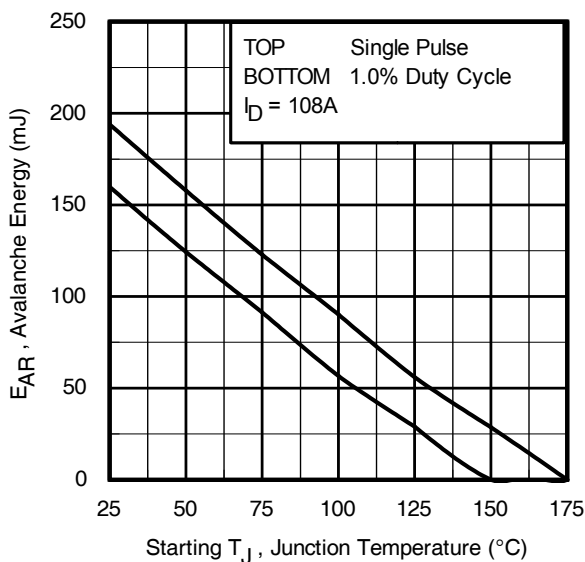
	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	180 ①	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ②	—	—	670		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 75A, V _{GS} = 0V ⑤
t _{rr}	Reverse Recovery Time	—	50	75	ns	T _J = 25°C V _{DD} = 85V
		—	60	90		T _J = 125°C I _F = 75A,
Q _{rr}	Reverse Recovery Charge	—	94	140	nC	T _J = 25°C di/dt = 100A/μs ⑤
		—	140	210		T _J = 125°C
I _{RRM}	Reverse Recovery Current	—	3.5	—	A	T _J = 25°C

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 120A. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ Limited by T_{Jmax}, starting T_J = 25°C, L = 0.033mH, R_G = 25Ω, I_{AS} = 108A, V_{GS} = 10V. Part not recommended for use above this value.
- ④ I_{SD} ≤ 75A, di/dt ≤ 630A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 175°C.
- ⑤ Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ⑥ C_{oss eff. (TR)} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
- ⑦ C_{oss eff. (ER)} is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
- ⑧ R_θ is measured at T_J approximately 90°C.


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance vs. Temperature

Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage


Fig 7. Typical Source-Drain Diode Forward Voltage

Fig 8. Maximum Safe Operating Area

Fig 9. Maximum Drain Current vs. Case Temperature

Fig 10. Drain-to-Source Breakdown Voltage

Fig 11. Typical C_{oss} Stored Energy

Fig 12. Threshold Voltage vs. Temperature


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Fig 14. Avalanche Current vs. Pulse width

**Notes on Repetitive Avalanche Curves, Figures 14, 15:
 (For further info, see AN-1005 at www.irf.com)**

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 22a, 22b.
4. $P_D(ave)$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not exceed T_{jmax} (assumed as 25°C in figure 14, 15).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_D(ave) = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_D(ave) \cdot t_{av}$$

Fig 15. Maximum Avalanche Energy vs. Temperature

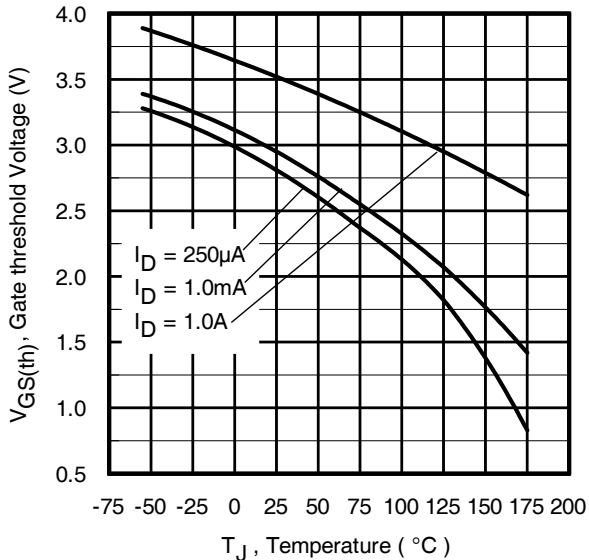


Fig 16. Threshold Voltage vs. Temperature

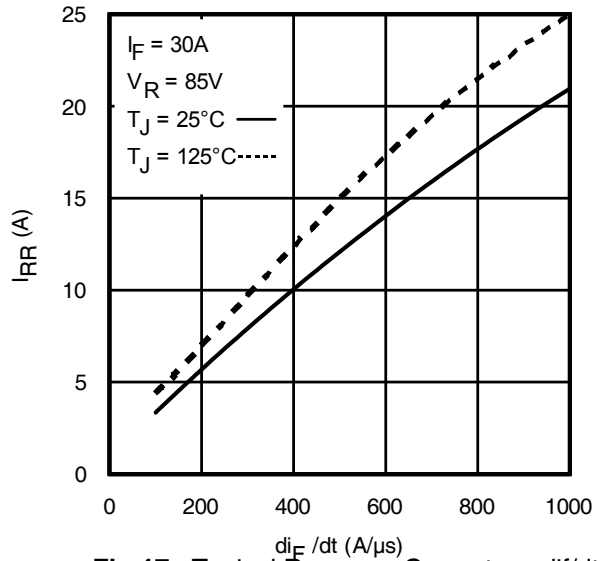


Fig 17. Typical Recovery Current vs. di/dt

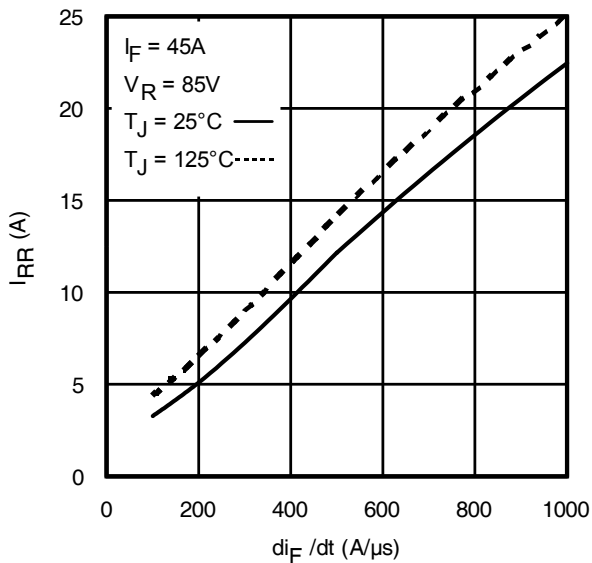


Fig 18. Typical Recovery Current vs. di/dt

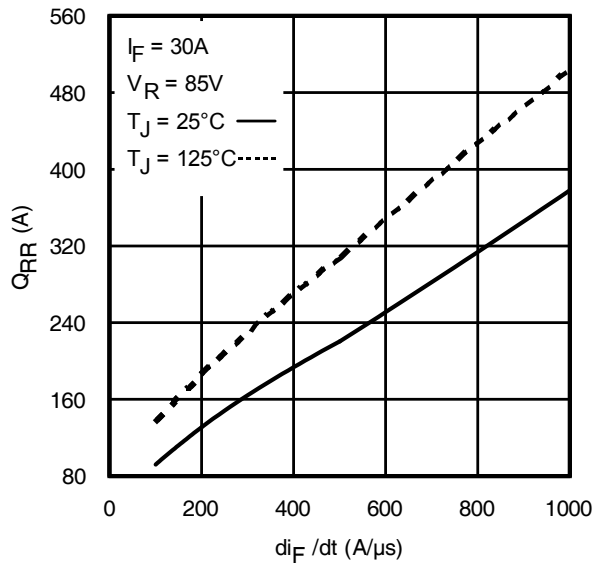


Fig 19. Typical Stored Charge vs. di/dt

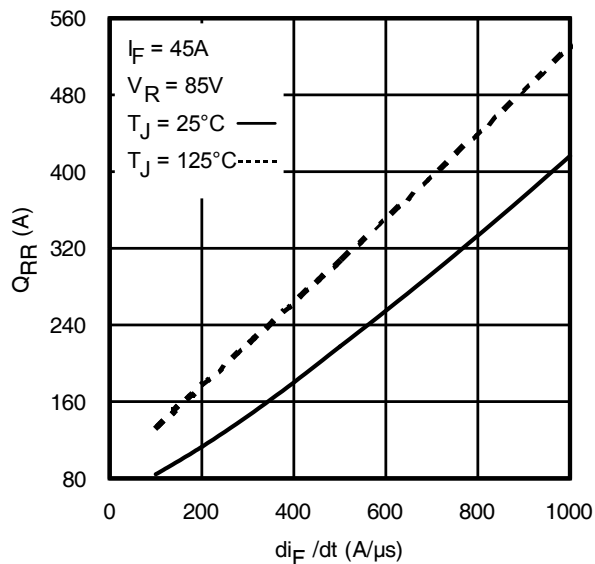
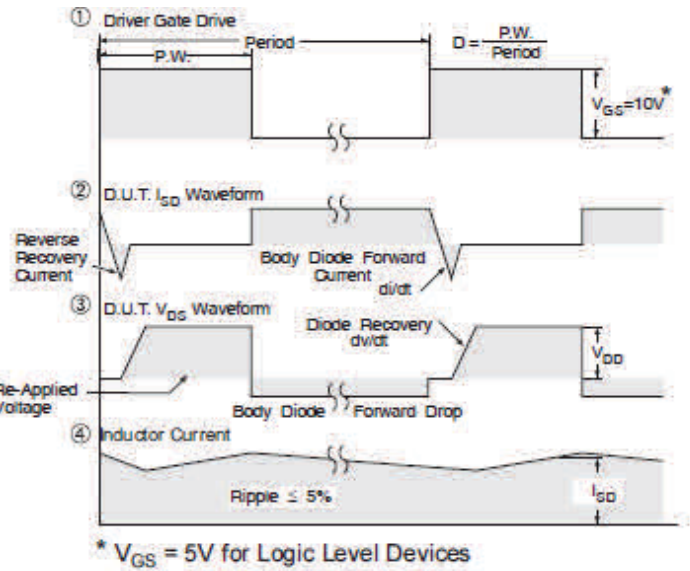
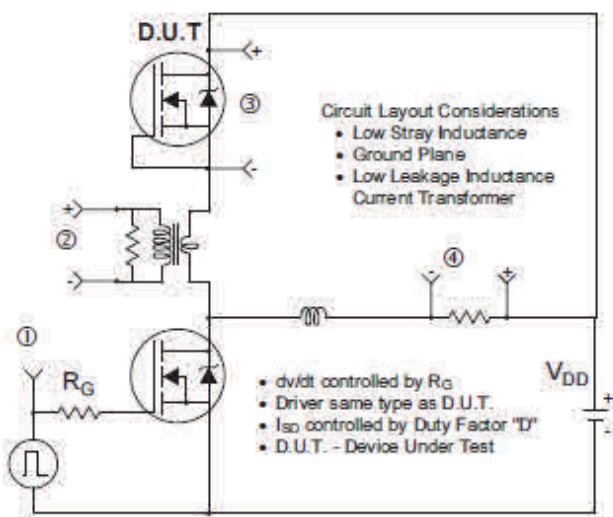
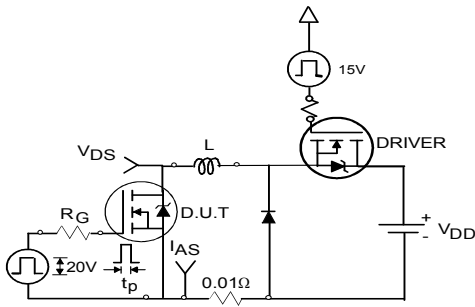
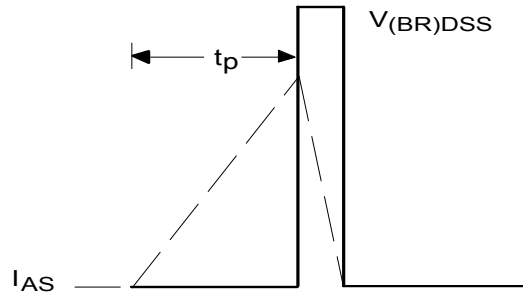
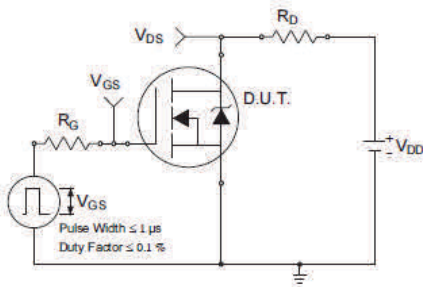
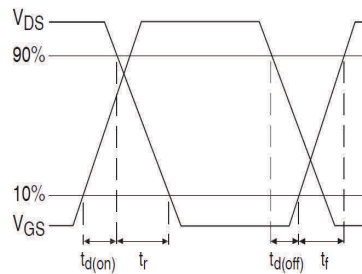
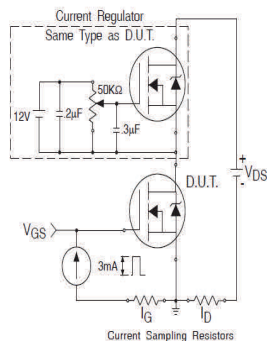
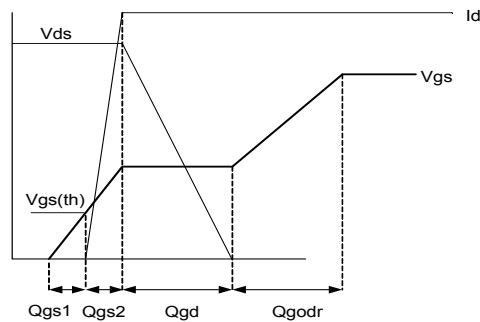
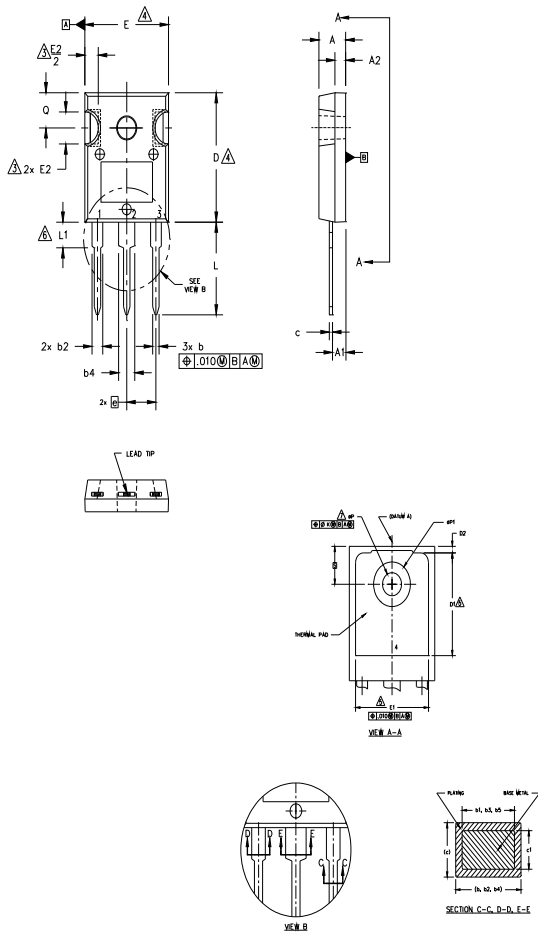


Fig 20. Typical Stored Charge vs. di/dt


Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

Fig 22a. Unclamped Inductive Test Circuit

Fig 22b. Unclamped Inductive Waveforms

Fig 23a. Switching Time Test Circuit

Fig 23b. Switching Time Waveforms

Fig 24a. Gate Charge Test Circuit

Fig 24b. Gate Charge Waveform

TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
 2. DIMENSIONS ARE SHOWN IN INCHES.
 3. CONTOUR OF SLOT OPTIONAL.
 4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
 6. LEAD FINISH UNCONTROLLED IN L1.
 7. øP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
 8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.065	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	-	13.08	-	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	-	13.46	-	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
øk	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
øP	.140	.144	3.56	3.66	
øP1	-	.291	-	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

- 1- GATE
- 2- DRAIN
- 3- SOURCE
- 4- DRAIN

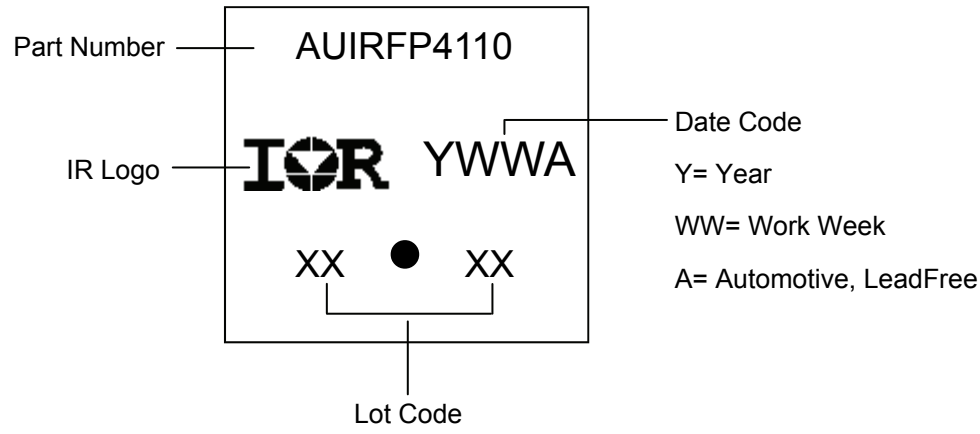
IGBTs, CoPACK

- 1- GATE
- 2- COLLECTOR
- 3- EMITTER
- 4- COLLECTOR

DIODES

- 1- ANODE/OPEN
- 2- CATHODE
- 3- ANODE

TO-247AC Part Marking Information



TO-247AC package is not recommended for Surface Mount Application.

Qualification Information

Qualification Level		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		TO-247AC	N/A
ESD	Machine Model	Class M4 (+/- 800) [†] AEC-Q101-002	
	Human Body Model	Class H3A (+/- 6000V) [†] AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000) [†] AEC-Q101-005	
RoHS Compliant		Yes	

† Highest passing voltage.

Revision History

Date	Comments
9/15/2017	<ul style="list-style-type: none"> Updated datasheet with corporate template Corrected typo error on part marking on page 8.

Published by

Infineon Technologies AG
81726 München, Germany

© Infineon Technologies AG 2015

All Rights Reserved.

IMPORTANT NOTICE

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenhheitsgarantie"). With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

For further information on the product, technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies office (www.infineon.com).

WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.